

## Detachment rate for negative ions in Ar/BF<sub>3</sub> discharges

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In this work we present rate coefficients for negative ions in Ar/BF<sub>3</sub> mixtures for the conditions used in plasma assisted technologies for semiconductor production. Boron produced in plasma devices continues to be the main p-type dopant in ion implantation of semiconductor devices. Yet plasma parameters of most frequently used Boron rich gas BF<sub>3</sub>, often in mixture with Ar are not well established. The cross sections for scattering of F<sup>-</sup> and BF<sub>4</sub><sup>-</sup> ions on Ar atom and on BF<sub>3</sub> molecule are calculated by using Nanbu's theory separating elastic from reactive collisions. A Monte Carlo simulation technique was applied to perform calculations of transport parameters in DC electric fields.

Boron trifluoride (BF<sub>3</sub>) alone or with addition of other gasses (O<sub>2</sub>, Ar, N<sub>2</sub>, CH<sub>4</sub>, N<sub>2</sub>) is the most commonly used gas in plasmas for implantation of the N-type dopant boron[1] as well as for detectors of neutrons and as catalyzer for several chemical reactions.. Negative ions usually observed in weakly electronegative BF<sub>3</sub> plasmas are F<sup>-</sup>, F<sub>2</sub><sup>-</sup>, BF<sub>2</sub><sup>-</sup> and BF<sub>4</sub><sup>-</sup>. While the main source for the first three ions is high energy dissociative electron attachment (~10 eV) the super halogen ion BF<sub>4</sub><sup>-</sup> is a product of both, F<sup>-</sup> and F<sub>2</sub><sup>-</sup> ion collisions with BF<sub>3</sub> and electron attachment [1].

Most abundant negative ions observed in BF<sub>3</sub> plasmas are F<sup>-</sup> and BF<sub>4</sub><sup>-</sup>. Their number density is hard to predict in a pulsed BF<sub>3</sub> discharge afterglow due to poorly known reaction rates. Since F<sup>-</sup> ions undergo detachment with BF<sub>3</sub> at minimum energy of 4.35 eV these ions and clusters formed around F<sup>-</sup> ion [2] could be responsible for electron production in the afterglow. Influx of the electrons close to the energy of about 4.35 eV is visible in EEPF's measured only in the afterglow measurement [3]. The electron loss process in afterglow is slow and negative ions are trapped by the remaining space charge field.

Super halogen ions are very stable in respect to detachment [4] and one may expect that these heavy ions are present in the afterglow with long lifetimes defined by diffusion to the walls.

The cross sections for scattering of BF<sub>4</sub><sup>-</sup> ions on Ar and BF<sub>3</sub>, and for F<sup>-</sup> ions on BF<sub>3</sub> are calculated by using Nanbu's theory [5, 6] separating elastic from detachment collisions. The cross sections for F<sup>-</sup> on Ar [6] were used to calculate rate coefficients for detachment. The dipole polarizability of  $3.31 \cdot 10^{-30} \text{ m}^3$  [7] and  $1.64 \cdot 10^{-30} \text{ m}^3$  [8] is used for BF<sub>3</sub> and Ar target respectively. Monte Carlo simulation was applied to perform calculations of transport coefficients as well as rate coefficients in DC electric fields. In Figure 1. we show detachment rate coefficient as a function  $E/N$  for F<sup>-</sup> and BF<sub>4</sub><sup>-</sup> ions in Ar and BF<sub>3</sub>.

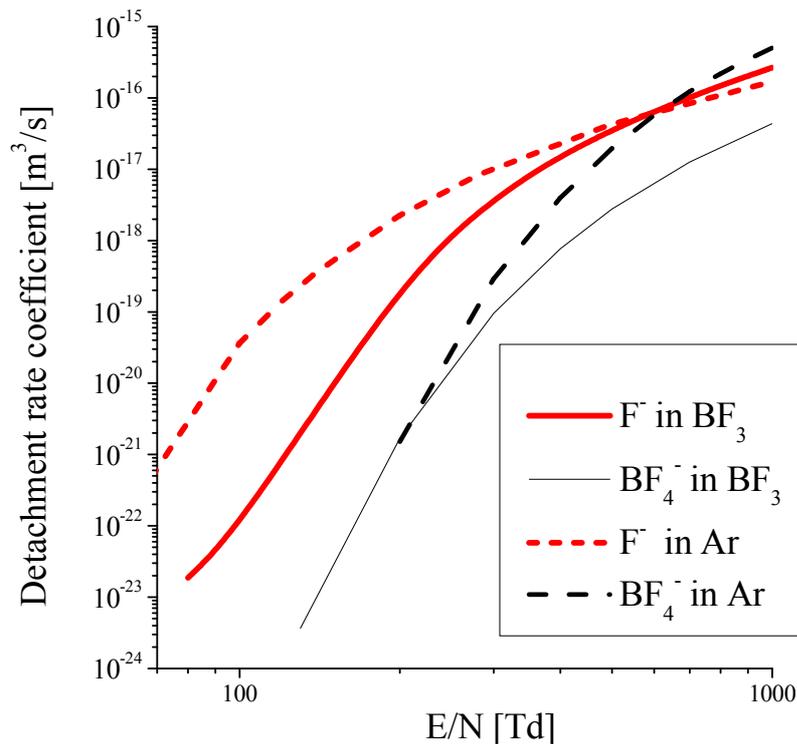


Fig. 1: Calculated detachment rate coefficients for  $F^-$  and  $BF_4^-$  ions in Ar/ $BF_3$  mixture.

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